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FORM PTO-892
(REV. 2-92)U.S. DEPARTMENT OF COMMERCE
PATENT AND TRADEMARK OFFICE

SERIAL NO. 09/231,618 GROUP ART UNIT 2823 ATTACHMENT TO PAPER NUMBER

APPLICANT(S)

McGATH/AY et al.

1C8210 S. 09/819530
05/07/01 PRO

NOTICE OF REFERENCES CITED

U.S. PATENT DOCUMENTS

*	DOCUMENT NO.	DATE	NAME	CLASS	SUB-CLASS	FILING DATE IF APPROPRIATE
A	S 391 517	2/21/95	GELATOS et al.			
B						
C						
D						
E						
F						
G						
H						
I						
J						
K						

FOREIGN PATENT DOCUMENTS

*	DOCUMENT NO.	DATE	COUNTRY	NAME	CLASS	SUB-CLASS	PERTINENT SHTS. DWG.	PP. SPEC.
L								
M								
N								
O								
P								
Q								

OTHER REFERENCES (Including Author, Title, Date, Pertinent Pages, Etc.)

R	
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U	

EXAMINER

DM GULATI

DATE

11/16/00

* A copy of this reference is not being furnished with this office action.
(See Manual of Patent Examining Procedure, section 707.05 (a).)

FORM PTO-1449

INFORMATION DISCLOSURE CITATION

Atty Docket
FI9-98-172Serial No.
09/231,618Applicant
Ivers et alFiling Date
January 14, 1999Group Art U
1773U.S. PTO
09/849530
05/07/01

U.S. PATENT DOCUMENTS

Examiner Initial		Document Number	Date	Name	Class	Sub-Class	Filing Date
DNC	AA	3,765,956	10/73	Li	148	33	
	AB	5,324,684	6/94	Kermani et al	437	95	
	AC	5,447,887	9/95	Filipiak et al	437	200	
	AD	5,489,550	2/96	Moslehi	437	165	
	AE	5,529,954	6/96	Iijima et al	437	189	
↓	AF	5,633,047	5/97	Brady et al	427	437	
	AG						
	AH						
	AI						
	AJ						
	AK						

FOREIGN PATENT DOCUMENTS

		Document Number	Date	Country	Class	Sub-Class	Trans-lation
	AL						Yes No
	AM						Yes No
	AN						Yes No
	AO						Yes No
	AP						Yes No

OTHER (Including Author, Title, Date, Pertinent Pages, etc.)

DNC	AR	Chemical Vapor Deposition of Cu ₃ Ge for High Aspect Ratio Metallization. <i>IBM Technical Disclosure Bulletin</i> 35, No. 4B, September 1992.
	AS	Aboelfotoh et al, Copper Passivation of Boron in Silicon and Boron Reactivation Kinetics, <i>Physical Review B</i> 44, No. 23, December 15, 1991.
↓	AT	Liou et al, Oxidation of Cu and Cu ₃ Ge Thin Films, <i>J. Appl. Phys.</i> 77, No. 10, May 1995.

Examiner

D. M. COLLETT

Date Considered

11/16/00

EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP § 609.
 Draw line through citation if not in conformance and not considered.
 Include copy of this form with next communication to Applicant.

INFORMATION DISCLOSURE STATEMENT <small>(Use several sheets if necessary)</small>				Docket Number (Optional) FI9-98-172		Application Number 09/231,618	
				Applicant(s) T. H. Ivers, et al.			
				Filing Date 01/14/99	Group Art Unit 1773		
U.S. PATENT DOCUMENTS							
*EXAMINER INITIAL	REF	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
<i>Dne</i>		5,855,993	01/05/99	Brady, et al.			
							
FOREIGN PATENT DOCUMENTS							
REF	DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	Translation	
						YES	NO
<i>Dne</i>	0 472 804 A2	04/03/92	Europe			<i>C</i>	<i>C</i>
						<i>C</i>	<i>C</i>
						<i>C</i>	<i>C</i>
						<i>C</i>	<i>C</i>
						<i>C</i>	<i>C</i>
						<i>C</i>	<i>C</i>
OTHER DOCUMENTS <i>(Including Author, Title, Date, Pertinent Pages, Etc.)</i>							
EXAMINER <i>D. M. Conner</i>				DATE CONSIDERED <i>11-16-00</i>			

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FORM PTO-1449

INFORMATION DISCLOSURE CITATION

Atty Docket FI9-98-172	Serial No. 09/231,618
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Applicant Ivers et al

Filing Date January 14, 1999	Group Art Unit 1773
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U.S. PATENT DOCUMENTS

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D, M	AA	3,765,956	10/73	Li	148	33	
	AB	5,324,684	6/94	Kermani et al	437	95	
	AC	5,447,887	9/95	Filipiak et al	437	200	
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	AL						Yes No
	AM						Yes No
	AN						Yes No
	AO						Yes No
	AP						Yes No

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D, M	AR	Chemical Vapor Deposition of Cu ₃ Ge for High Aspect Ratio Metallization, <i>IBM Technical Disclosure Bulletin</i> 35, No. 4B, September 1992.
	AS	Aboelfotoh et al, Copper Passivation of Boron in Silicon and Boron Reactivation Kinetics, <i>Physical Review B</i> 44, No. 23, December 15, 1991.
	AT	Liou et al, Oxidation of Cu and Cu ₃ Ge Thin Films, <i>J. Appl. Phys.</i> 77, No. 10, May 1995.

Examiner	D, M (c-617-8)	Date Considered
		10-29-01

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